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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M3
Core Size	32-Bit Single-Core
Speed	32MHz
Connectivity	I²C, IrDA, LINbus, SPI, UART/USART, USB
Peripherals	Brown-out Detect/Reset, DMA, I²S, LCD, POR, PWM, WDT
Number of I/O	83
Program Memory Size	256KB (256K x 8)
Program Memory Type	FLASH
EEPROM Size	8K x 8
RAM Size	32K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 3.6V
Data Converters	A/D 25x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	100-LQFP
Supplier Device Package	-
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32l162vct6

Table 5. Functionalities depending on the working mode (from Run/active down to standby) (continued)

Ips	Run/Active	Sleep	Low-power Run	Low-power Sleep	Stop		Standby	
						Wakeup capability		Wakeup capability
ADC	Y	Y	--	--	--	--	--	--
DAC	Y	Y	Y	Y	Y	--	--	--
Tempsensor	Y	Y	Y	Y	Y	--	--	--
OP amp	Y	Y	Y	Y	Y	--	--	--
Comparators	Y	Y	Y	Y	Y	Y	--	--
16-bit and 32-bit Timers	Y	Y	Y	Y	--	--	--	--
IWDG	Y	Y	Y	Y	Y	Y	Y	Y
WWDG	Y	Y	Y	Y	--	--	--	--
Touch sensing	Y	Y	--	--	--	--	--	--
Systic Timer	Y	Y	Y	Y		--	--	--
GPIOs	Y	Y	Y	Y	Y	Y	--	3 pins
Wakeup time to Run mode	0 µs	0.4 µs	3 µs	46 µs	< 8 µs		58 µs	
Consumption V_{DD}=1.8 to 3.6 V (Typ)	Down to 185 µA/MHz (from Flash)	Down to 34.5 µA/MHz (from Flash)	Down to 8.6 µA	Down to 4.4 µA	0.43 µA (no RTC) V_{DD}=1.8V		0.29 µA (no RTC) V_{DD}=1.8V	
					1.15 µA (with RTC) V_{DD}=1.8V		0.9 µA (with RTC) V_{DD}=1.8V	
					0.44 µA (no RTC) V_{DD}=3.0V		0.29 µA (no RTC) V_{DD}=3.0V	
					1.4 µA (with RTC) V_{DD}=3.0V		1.15 µA (with RTC) V_{DD}=3.0V	

1. The startup on communication line wakes the CPU which was made possible by an EXTI, this induces a delay before entering run mode.

3.2 ARM® Cortex®-M3 core with MPU

The ARM® Cortex®-M3 processor is the industry leading processor for embedded systems. It has been developed to provide a low-cost platform that meets the needs of MCU implementation, with a reduced pin count and low-power consumption, while delivering outstanding computational performance and an advanced system response to interrupts.

The ARM® Cortex®-M3 32-bit RISC processor features exceptional code-efficiency, delivering the high-performance expected from an ARM core in the memory size usually associated with 8- and 16-bit devices.

power ramp-up should guarantee that 1.65 V is reached on V_{DD} at least 1 ms after it exits the POR area.

Five BOR thresholds are available through option bytes, starting from 1.8 V to 3 V. To reduce the power consumption in Stop mode, it is possible to automatically switch off the internal reference voltage (V_{REFINT}) in Stop mode. The device remains in reset mode when V_{DD} is below a specified threshold, $V_{POR/PDR}$ or V_{BOR}, without the need for any external reset circuit.

Note: The start-up time at power-on is typically 3.3 ms when BOR is active at power-up, the start-up time at power-on can be decreased down to 1 ms typically for devices with BOR inactive at power-up.

The device features an embedded programmable voltage detector (PVD) that monitors the V_{DD}/V_{DDA} power supply and compares it to the V_{PVD} threshold. This PVD offers 7 different levels between 1.85 V and 3.05 V, chosen by software, with a step around 200 mV. An interrupt can be generated when V_{DD}/V_{DDA} drops below the V_{PVD} threshold and/or when V_{DD}/V_{DDA} is higher than the V_{PVD} threshold. The interrupt service routine can then generate a warning message and/or put the MCU into a safe state. The PVD is enabled by software.

3.3.3 Voltage regulator

The regulator has three operation modes: main (MR), low-power (LPR) and power down.

- MR is used in Run mode (nominal regulation)
- LPR is used in the Low-power run, Low-power sleep and Stop modes
- Power down is used in Standby mode. The regulator output is high impedance, the kernel circuitry is powered down, inducing zero consumption but the contents of the registers and RAM are lost except for the standby circuitry (wakeup logic, IWDG, RTC, LSI, LSE crystal 32K osc, RCC_CSR).

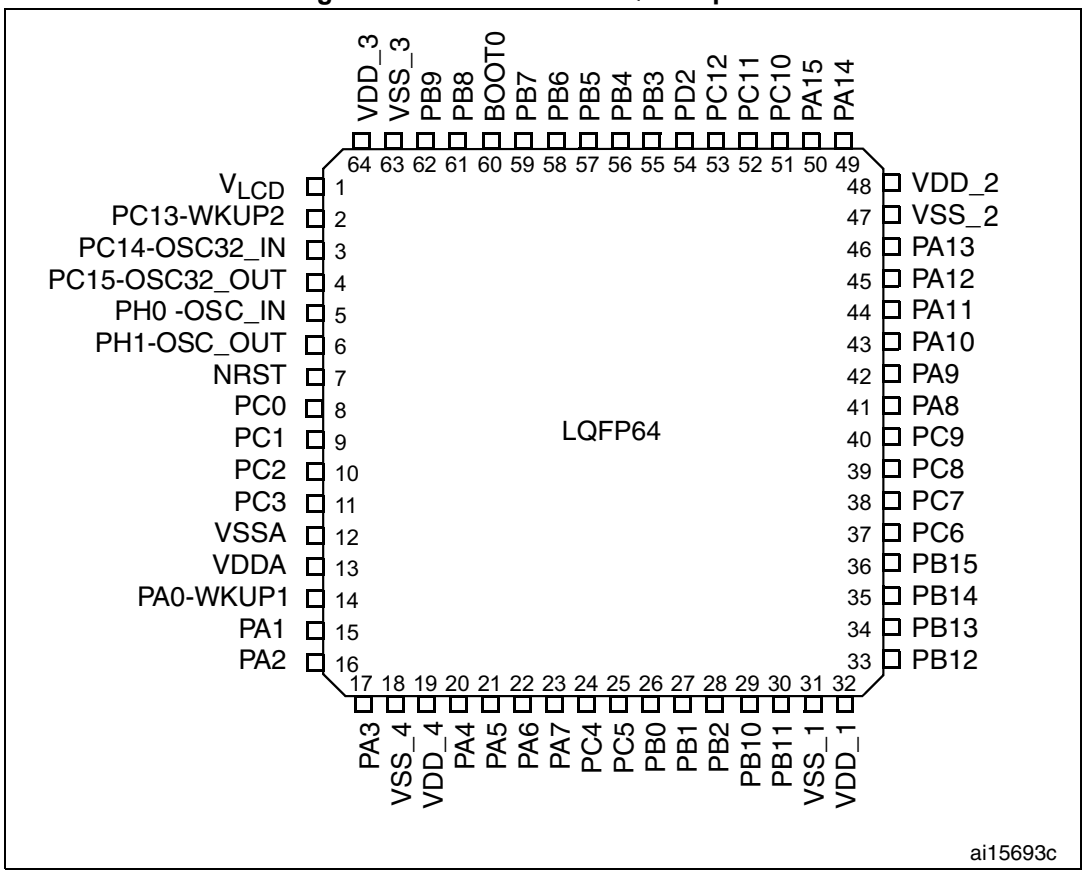
3.3.4 Boot modes

At startup, boot pins are used to select one of three boot options:

- Boot from Flash memory
- Boot from System memory
- Boot from embedded RAM

The boot loader is located in System memory. It is used to reprogram the Flash memory by using USART1, USART2 or USB. See Application note “STM32 microcontroller system memory boot mode” (AN2606) for details.

Figure 5. STM32L162RC LQFP64 pinout



1. This figure shows the package top view.

Table 10. Alternate function input/output (continued)

Port name	Digital alternate function number								. .		. .		
	AFIO0	AFIO1	AFIO2	AFIO3	AFIO4	AFIO5	AFIO6	AFIO7		AFIO11		AFIO14	AFIO15
	Alternate function												
	SYSTEM	TIM2	TIM3/4/5	TIM9/ 10/11	I2C1/2	SPI1/2	SPI3	USART1/2/3		LCD		CPRI	SYSTEM
PC4	-	-	-	-	-	-	-	-		SEG22		TIMx_IC1	EVENT OUT
PC5	-	-	-	-	-	-	-	-		SEG23		TIMx_IC2	EVENT OUT
PC6	-	-	TIM3_CH1	-	-	I2S2_MCK	-	-		SEG24		TIMx_IC3	EVENT OUT
PC7	-	-	TIM3_CH2	-	-	-	I2S3_MCK	-		SEG25		TIMx_IC4	EVENT OUT
PC8	-	-	TIM3_CH3	-	-	-	-	-		SEG26		TIMx_IC1	EVENT OUT
PC9	-	-	TIM3_CH4	-	-	-	-	-		SEG27		TIMx_IC2	EVENT OUT
PC10	-	-	-	-	-	-	SPI3_SCK I2S3_CK	USART3_TX		COM4/ SEG28/ SEG40		TIMx_IC3	EVENT OUT
PC11	-	-	-	-	-	-	SPI3_MISO	USART3_RX		COM5/ SEG29 /SEG41		TIMx_IC4	EVENT OUT
PC12	-	-	-	-	-	-	SPI3_MOSI I2S3_SD	USART3_CK		COM6/ SEG30/ SEG42		TIMx_IC1	EVENT OUT
PC13-WKUP2	-	-	-	-	-	-	-	-		-		TIMx_IC2	EVENT OUT
PC14 OSC32_IN	-	-	-	-	-	-	-	-		-		TIMx_IC3	EVENT OUT
PC15 OSC32_ OUT	-	-	-	-	-	-	-	-		-		TIMx_IC4	EVENT OUT
PD0	-	-	-	TIM9_CH1	-	SPI2_NSS I2S2_WS	-	-		-		TIMx_IC1	EVENT OUT
PD1	-	-	-	-	-	SPI2 SCK I2S2_CK	-	-		-		TIMx_IC2	EVENT OUT
PD2	-	-	TIM3_ETR	-	-	-	-	-		COM7/ SEG31/ SEG43		TIMx_IC3	EVENT OUT

Table 10. Alternate function input/output (continued)

Port name	Digital alternate function number												
	AFIO0	AFIO1	AFIO2	AFIO3	AFIO4	AFIO5	AFIO6	AFIO7	. .	AFIO11	. .	AFIO14	AFIO15
	Alternate function												
	SYSTEM	TIM2	TIM3/4/5	TIM9/ 10/11	I2C1/2	SPI1/2	SPI3	USART1/2/3		LCD		CPRI	SYSTEM
PD3	-	-	-	-	-	SPI2_MISO	-	USART2_CTS		-		TIMx_IC4	EVENT OUT
PD4	-	-	-	-	-	SPI2_MOSI I2S2_SD	-	USART2_RTS		-		TIMx_IC1	EVENT OUT
PD5	-	-	-	-	-		-	USART2_TX		-		TIMx_IC2	EVENT OUT
PD6	-	-	-		-	-	-	USART2_RX		-		TIMx_IC3	EVENT OUT
PD7	-	-	-	TIM9_CH2	-	-	-	USART2_CK		-		TIMx_IC4	EVENT OUT
PD8	-	-	-	-	-	-	-	USART3_TX		SEG28		TIMx_IC1	EVENT OUT
PD9	-	-	-	-	-	-	-	USART3_RX		SEG29		TIMx_IC2	EVENT OUT
PD10	-	-	-	-	-	-	-	USART3_CK		SEG30		TIMx_IC3	EVENT OUT
PD11	-	-	-	-	-	-	-	USART3_CTS		SEG31		TIMx_IC4	EVENT OUT
PD12	-	-	TIM4_CH1	-	-	-	-	USART3_RTS		SEG32		TIMx_IC1	EVENT OUT
PD13	-	-	TIM4_CH2	-	-	-	-	-		SEG33		TIMx_IC2	EVENT OUT
PD14	-	-	TIM4_CH3	-	-	-	-	-		SEG34		TIMx_IC3	EVENT OUT
PD15	-	-	TIM4_CH4	-	-	-	-	-		SEG35		TIMx_IC4	EVENT OUT
PE0	-	-	TIM4_ETR	TIM10_CH1	-	-	-	-		SEG36		TIMx_IC1	EVENT OUT
PE1	-	-	-	TIM11_CH1	-	-	-	-		SEG37		TIMx_IC2	EVENT OUT
PE2	TRACECK	-	TIM3_ETR	-				-		SEG 38		TIMx_IC3	EVENT OUT
PE3	TRACED0	-	TIM3_CH1	-	-	-	-	-		SEG 39		TIMx_IC4	EVENT OUT
PE4	TRACED1	-	TIM3_CH2	-	-	-	-	-		-		TIMx_IC1	EVENT OUT
PE5	TRACED2	-	-	TIM9_CH1	-	-	-	-		-		TIMx_IC2	EVENT OUT
PE6-WKUP3	TRACED3	-	-	TIM9_CH2	-	-	-	-		-		TIMx_IC3	EVENT OUT
PE7	-	-	-	-	-	-	-	-		-		TIMx_IC4	EVENT OUT

Table 10. Alternate function input/output (continued)

Port name	Digital alternate function number								. .		. .		
	AFIO0	AFIO1	AFIO2	AFIO3	AFIO4	AFIO5	AFIO6	AFIO7		AFIO11		AFIO14	AFIO15
	Alternate function												
	SYSTEM	TIM2	TIM3/4/5	TIM9/ 10/11	I2C1/2	SPI1/2	SPI3	USART1/2/3		LCD		CPRI	SYSTEM
PE8	-	-	-	-	-	-	-	-		-		TIMx_IC1	EVENT OUT
PE9	-	TIM2_CH1_ETR	TIM5_ETR	-	-	-	-	-		-		TIMx_IC2	EVENT OUT
PE10	-	TIM2_CH2	-	-	-	-	-	-		-		TIMx_IC3	EVENT OUT
PE11	-	TIM2_CH3	-	-	-	-	-	-		-		TIMx_IC4	EVENT OUT
PE12	-	TIM2_CH4	-	-	-	SPI1_NSS	-	-		-		TIMx_IC1	EVENT OUT
PE13	-	-	-	-	-	SPI1_SCK	-	-		-		TIMx_IC2	EVENT OUT
PE14	-	-	-	-	-	SPI1_MISO	-	-		-		TIMx_IC3	EVENT OUT
PE15	-	-	-	-	-	SPI1_MOSI	-	-		-		TIMx_IC4	EVENT OUT
PH0OSC _IN	-	-	-	-	-	-	-	-		-		-	-
PH1OSC_ OUT	-	-	-	-	-	-	-	-		-		-	-
PH2	-	-	-	-	-	-	-	-		-		-	-

Table 18. Current consumption in Run mode, code with data processing running from Flash

Symbol	Parameter	Conditions		f_{HCLK}	Typ	Max(1)	Unit
I_{DD} (Run from Flash)	Supply current in Run mode, code executed from Flash	f_{HSE} = f_{HCLK} up to 16 MHz included, f_{HSE} = f_{HCLK}/2 above 16 MHz (PLL ON)(2)	Range 3, V_{CORE}=1.2 V VOS[1:0] = 11	1 MHz	215	400	µA
				2 MHz	400	600	
				4 MHz	725	960	
			Range 2, V_{CORE}=1.5 V VOS[1:0] = 10	4 MHz	0.915	1.1	mA
				8 MHz	1.75	2.1	
				16 MHz	3.4	3.9	
			Range 1, V_{CORE}=1.8 V VOS[1:0] = 01	8 MHz	2.1	2.8	
				16 MHz	4.2	4.9	
				32 MHz	8.25	9.4	
		HSI clock source (16 MHz)	Range 2, V_{CORE}=1.5 V VOS[1:0] = 10	16 MHz	3.5	4	
			Range 1, V_{CORE}=1.8 V VOS[1:0] = 01	32 MHz	8.2	9.6	
		MSI clock, 65 kHz	Range 3, V_{CORE}=1.2 V VOS[1:0] = 11	65 kHz	40.5	110	µA
		MSI clock, 524 kHz		524 kHz	125	190	
		MSI clock, 4.2 MHz		4.2 MHz	775	900	

1. Guaranteed by characterization results, unless otherwise specified.
2. Oscillator bypassed (HSEBYP = 1 in RCC_CR register).

Table 23. Typical and maximum current consumptions in Stop mode

Symbol	Parameter	Conditions			Typ	Max(1)	Unit
I_{DD} (Stop with RTC)	Supply current in Stop mode with RTC enabled	RTC clocked by LSI or LSE external clock (32.768kHz), regulator in LP mode, HSI and HSE OFF (no independent watchdog)	LCD OFF	T_A = -40°C to 25°C V_{DD} = 1.8 V	1.15	-	µA
				T_A = -40°C to 25°C	1.4	-	
				T_A = 55°C	2	-	
				T_A= 85°C	3.4	10	
				T_A = 105°C	6.35	23	
			LCD ON (static duty)(2)	T_A = -40°C to 25°C	1.55	6	
				T_A = 55°C	2.15	7	
				T_A= 85°C	3.55	12	
				T_A = 105°C	6.3	27	
			LCD ON (1/8 duty)(3)	T_A = -40°C to 25°C	3.9	10	
				T_A = 55°C	4.65	11	
				T_A= 85°C	6.25	16	
				T_A = 105°C	9.1	44	
		RTC clocked by LSE external quartz (32.768kHz), regulator in LP mode, HSI and HSE OFF (no independent watchdog(4)	LCD OFF	T_A = -40°C to 25°C	1.5	-	
				T_A = 55°C	2.15	-	
				T_A= 85°C	3.7	-	
				T_A = 105°C	6.75	-	
			LCD ON (static duty)(2)	T_A = -40°C to 25°C	1.6	-	
				T_A = 55°C	2.3	-	
				T_A= 85°C	3.8	-	
				T_A = 105°C	6.85	-	
			LCD ON (1/8 duty)(3)	T_A = -40°C to 25°C	4	-	
				T_A = 55°C	4.85	-	
				T_A= 85°C	6.5	-	
				T_A = 105°C	9.1	-	
			LCD OFF	T_A = -40°C to 25°C V_{DD} = 1.8V	1.2	-	
				T_A = -40°C to 25°C V_{DD} = 3.0V	1.5	-	
				T_A = -40°C to 25°C V_{DD} = 3.6V	1.75	-	

Table 23. Typical and maximum current consumptions in Stop mode (continued)

Symbol	Parameter	Conditions		Typ	Max(1)	Unit
I_{DD} (Stop)	Supply current in Stop mode (RTC disabled)	Regulator in LP mode, HSI and HSE OFF, independent watchdog and LSI enabled	T_A = -40°C to 25°C	1.8	2.2	µA
		Regulator in LP mode, LSI, HSI and HSE OFF (no independent watchdog)	T_A = -40°C to 25°C	0.435	1	
			T_A = 55°C	0.99	3	
			T_A= 85°C	2.4	9	
			T_A = 105°C	5.5	22(5)	
I_{DD} (WU from Stop)	Supply current during wakeup from Stop mode	MSI = 4.2 MHz	T_A = -40°C to 25°C	2	-	mA
		MSI = 1.05 MHz		1.45	-	
		MSI = 65 kHz(6)		1.45	-	

1. Guaranteed by characterization results, unless otherwise specified.
2. LCD enabled with external VLCD, static duty, division ratio = 256, all pixels active, no LCD connected.
3. LCD enabled with external VLCD, 1/8 duty, 1/3 bias, division ratio = 64, all pixels active, no LCD connected.
4. Based on characterization done with a 32.768 kHz crystal (MC306-G-06Q-32.768, manufacturer JFVNY) with two 6.8 pF loading capacitors.
5. Guaranteed by test in production.
6. When MSI = 64 kHz, the RMS current is measured over the first 15 µs following the wakeup event. For the remaining part of the wakeup period, the current corresponds the Run mode current.

Table 29. HSE oscillator characteristics(1)(2)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{OSC_IN}	Oscillator frequency	-	1		24	MHz
R_F	Feedback resistor	-	-	200	-	kΩ
C	Recommended load capacitance versus equivalent serial resistance of the crystal (R_S)(3)	R_S = 30 Ω	-	20	-	pF
I_{HSE}	HSE driving current	V_{DD}= 3.3 V, V_{IN} = V_{SS} with 30 pF load	-	-	3	mA
$I_{DD(HSE)}$	HSE oscillator power consumption	C = 20 pF f_{OSC} = 16 MHz	-	-	2.5 (startup) 0.7 (stabilized)	mA
		C = 10 pF f_{OSC} = 16 MHz	-	-	2.5 (startup) 0.46 (stabilized)	
g_m	Oscillator transconductance	Startup	3.5	-	-	mA /V
$t_{SU(HSE)}$(4)	Startup time	V_{DD} is stabilized	-	1	-	ms

1. Resonator characteristics given by the crystal/ceramic resonator manufacturer.
2. Guaranteed by characterization results.
3. The relatively low value of the RF resistor offers a good protection against issues resulting from use in a humid environment, due to the induced leakage and the bias condition change. However, it is recommended to take this point into account if the MCU is used in tough humidity conditions.
4. $t_{SU(HSE)}$ is the startup time measured from the moment it is enabled (by software) to a stabilized 8 MHz oscillation is reached. This value is measured for a standard crystal resonator and it can vary significantly with the crystal manufacturer.

For C_{L1} and C_{L2}, it is recommended to use high-quality external ceramic capacitors in the 5 pF to 25 pF range (typ.), designed for high-frequency applications, and selected to match the requirements of the crystal or resonator (see *Figure 14*). C_{L1} and C_{L2} are usually the same size. The crystal manufacturer typically specifies a load capacitance which is the series combination of C_{L1} and C_{L2}. PCB and MCU pin capacitance must be included (10 pF can be used as a rough estimate of the combined pin and board capacitance) when sizing C_{L1} and C_{L2}. Refer to the application note AN2867 “Oscillator design guide for ST microcontrollers” available from the ST website *www.st.com*.

6.3.7 Internal clock source characteristics

The parameters given in *Table 31* are derived from tests performed under the conditions summarized in *Table 14*.

High-speed internal (HSI) RC oscillator

Table 31. HSI oscillator characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{HSI}	Frequency	V_{DD} = 3.0 V	-	16	-	MHz
$TRIM^{(1)(2)}$	HSI user-trimmed resolution	Trimming code is not a multiple of 16	-	±0.4	0.7	%
		Trimming code is a multiple of 16	-	-	±1.5	%
$ACC_{HSI}^{(2)}$	Accuracy of the factory-calibrated HSI oscillator	V_{DDA} = 3.0 V, T_A = 25 °C	$-1^{(3)}$	-	$1^{(3)}$	%
		V_{DDA} = 3.0 V, T_A = 0 to 55 °C	-1.5	-	1.5	%
		V_{DDA} = 3.0 V, T_A = -10 to 70 °C	-2	-	2	%
		V_{DDA} = 3.0 V, T_A = -10 to 85 °C	-2.5	-	2	%
		V_{DDA} = 3.0 V, T_A = -10 to 105 °C	-4	-	2	%
		V_{DDA} = 1.65 V to 3.6 V T_A = -40 to 105 °C	-4	-	3	%
$t_{SU(HSI)}^{(2)}$	HSI oscillator startup time	-	-	3.7	6	µs
$I_{DD(HSI)}^{(2)}$	HSI oscillator power consumption	-	-	100	140	µA

1. The trimming step differs depending on the trimming code. It is usually negative on the codes which are multiples of 16 (0x00, 0x10, 0x20, 0x30...0xE0).
2. Guaranteed by characterization results.
3. Guaranteed by test in production.

Low-speed internal (LSI) RC oscillator

Table 32. LSI oscillator characteristics

Symbol	Parameter	Min	Typ	Max	Unit
$f_{LSI}^{(1)}$	LSI frequency	26	38	56	kHz
$D_{LSI}^{(2)}$	LSI oscillator frequency drift 0°C ≤T_A ≤105°C	-10	-	4	%
$t_{su(LSI)}^{(3)}$	LSI oscillator startup time	-	-	200	µs
$I_{DD(LSI)}^{(3)}$	LSI oscillator power consumption	-	400	510	nA

1. Guaranteed by test in production.
2. This is a deviation for an individual part, once the initial frequency has been measured.
3. Guaranteed by design.

To complete these trials, ESD stress can be applied directly on the device, over the range of specification values. When unexpected behavior is detected, the software can be hardened to prevent unrecoverable errors occurring (see application note AN1015).

Electromagnetic Interference (EMI)

The electromagnetic field emitted by the device are monitored while a simple application is executed (toggling 2 LEDs through the I/O ports). This emission test is compliant with IEC 61967-2 standard which specifies the test board and the pin loading.

Table 39. EMI characteristics

Symbol	Parameter	Conditions	Monitored frequency band	Max vs. frequency range			Unit
				4 MHz voltage range 3	16 MHz voltage range 2	32 MHz voltage range 1	
S_{EMI}	Peak level	V_{DD} = 3.3 V, T_A = 25 °C, LQFP100 package compliant with IEC 61967-2	0.1 to 30 MHz	3	-6	-5	dBµV
			30 to 130 MHz	18	4	-7	
			130 MHz to 1GHz	15	5	-7	
			SAE EMI Level	2.5	2	1	-

6.3.11 Electrical sensitivity characteristics

Based on three different tests (ESD, LU) using specific measurement methods, the device is stressed in order to determine its performance in terms of electrical sensitivity.

Electrostatic discharge (ESD)

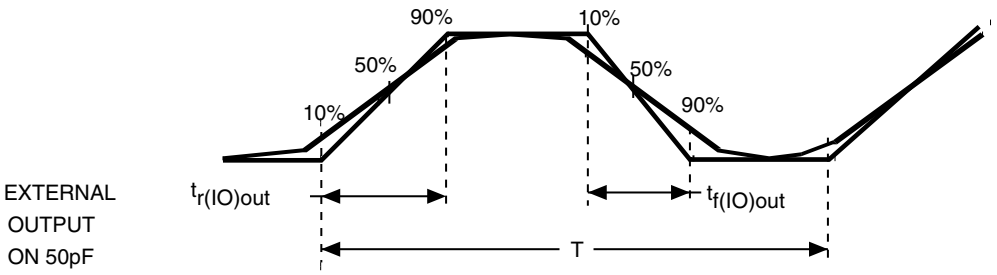
Electrostatic discharges (a positive then a negative pulse separated by 1 second) are applied to the pins of each sample according to each pin combination. The sample size depends on the number of supply pins in the device (3 parts × (n+1) supply pins). This test conforms to the JESD22-A114, ANSI/ESD STM5.3.1. standard.

Table 40. ESD absolute maximum ratings

Symbol	Ratings	Conditions	Class	Maximum value(1)	Unit
$V_{ESD(HBM)}$	Electrostatic discharge voltage (human body model)	T_A = +25 °C, conforming to JESD22-A114	2	2000	V
$V_{ESD(CDM)}$	Electrostatic discharge voltage (charge device model)	T_A = +25 °C, conforming to ANSI/ESD STM5.3.1.	C4	500	V

1. Guaranteed by characterization results.

Figure 16. I/O AC characteristics definition



Maximum frequency is achieved if $(t_r + t_f) \leq 2/3)T$ and if the duty cycle is (45-55%)
when loaded by 50pF

ai14131c

6.3.14 NRST pin characteristics

The NRST pin input driver uses CMOS technology. It is connected to a permanent pull-up resistor, R_{PU} (see *Table 46*)

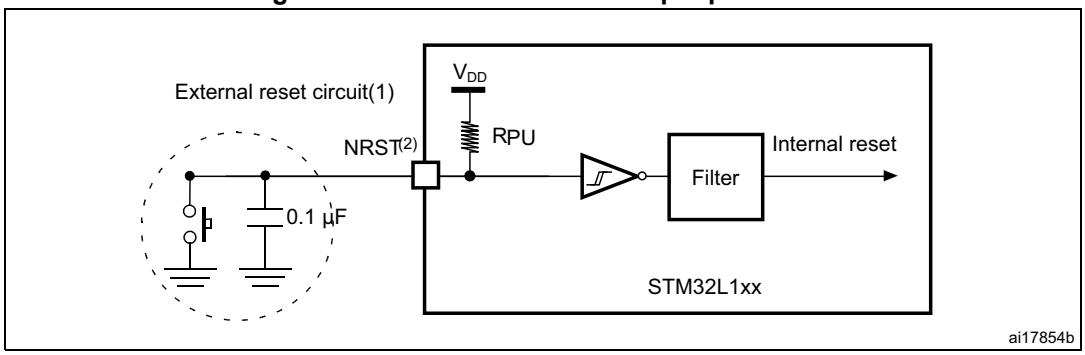
Unless otherwise specified, the parameters given in *Table 46* are derived from tests performed under the conditions summarized in *Table 14*.

Table 46. NRST pin characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{IL(NRST)}$(1)	NRST input low level voltage	-	-	-	0.3 V_{DD}	V
$V_{IH(NRST)}$(1)	NRST input high level voltage	-	0.39V_{DD}+0.59	-	-	
$V_{OL(NRST)}$(1)	NRST output low level voltage	I_{OL} = 2 mA 2.7 V < V_{DD} < 3.6 V	-	-	0.4	
		I_{OL} = 1.5 mA 1.65 V < V_{DD} < 2.7 V	-	-		
$V_{hys(NRST)}$(1)	NRST Schmitt trigger voltage hysteresis	-	-	10%V_{DD}(2)	-	mV
R_{PU}	Weak pull-up equivalent resistor(3)	V_{IN} = V_{SS}	30	45	60	kΩ
$V_{F(NRST)}$(1)	NRST input filtered pulse	-	-	-	50	ns
$V_{NF(NRST)}$(3)	NRST input not filtered pulse	-	350	-	-	ns

1. Guaranteed by design.
2. With a minimum of 200 mV.
3. The pull-up is designed with a true resistance in series with a switchable PMOS. This PMOS contribution to the series resistance is around 10%.

Figure 17. Recommended NRST pin protection



1. The reset network protects the device against parasitic resets.
2. The user must ensure that the level on the NRST pin can go below the $V_{IL(NRST)}$ max level specified in *Table 46*. Otherwise the reset will not be taken into account by the device.

6.3.15 TIM timer characteristics

The parameters given in the *Table 47* are guaranteed by design.

Refer to *Section 6.3.13: I/O port characteristics* for details on the input/output ction characteristics (output compare, input capture, external clock, PWM output).

Table 47. TIMx(1) characteristics

Symbol	Parameter	Conditions	Min	Max	Unit
$t_{res(TIM)}$	Timer resolution time	-	1	-	$t_{TIMxCLK}$
		$f_{TIMxCLK}$ = 32 MHz	31.25	-	ns
f_{EXT}	Timer external clock frequency on CH1 to CH4	-	0	$f_{TIMxCLK}/2$	MHz
		$f_{TIMxCLK}$ = 32 MHz	0	16	MHz
Res_{TIM}	Timer resolution	-		16	bit
$t_{COUNTER}$	16-bit counter clock period when internal clock is selected (timer's prescaler disabled)	-	1	65536	$t_{TIMxCLK}$
		$f_{TIMxCLK}$ = 32 MHz	0.0312	2048	µs
t_{MAX_COUNT}	Maximum possible count	-	-	65536 × 65536	$t_{TIMxCLK}$
		$f_{TIMxCLK}$ = 32 MHz	-	134.2	s

1. TIMx is used as a general term to refer to the TIM2, TIM3 and TIM4 timers.

SPI characteristics

Unless otherwise specified, the parameters given in the following table are derived from tests performed under the conditions summarized in *Table 14*.

Refer to *Section 6.3.12: I/O current injection characteristics* for more details on the input/output alternate function characteristics (NSS, SCK, MOSI, MISO).

Table 50. SPI characteristics(1)

Symbol	Parameter	Conditions	Min	Max(2)	Unit
f_{SCK} $1/t_{c(SCK)}$	SPI clock frequency	Master mode	-	16	MHz
		Slave mode	-	16	
		Slave transmitter	-	12(3)	
$t_{r(SCK)}$(2) $t_{f(SCK)}$(2)	SPI clock rise and fall time	Capacitive load: C = 30 pF	-	6	ns
DuCy(SCK)	SPI slave input clock duty cycle	Slave mode	30	70	%
$t_{su(NSS)}$	NSS setup time	Slave mode	$4t_{HCLK}$	-	ns
$t_{h(NSS)}$	NSS hold time	Slave mode	$2t_{HCLK}$	-	
$t_{w(SCKH)}$(2) $t_{w(SCKL)}$(2)	SCK high and low time	Master mode	$t_{SCK}/2-5$	$t_{SCK}/2+3$	
$t_{su(MI)}$(2)	Data input setup time	Master mode	5	-	
$t_{su(SI)}$(2)		Slave mode	6	-	
$t_{h(MI)}$(2)	Data input hold time	Master mode	5	-	
$t_{h(SI)}$(2)		Slave mode	5	-	
$t_{a(SO)}$(4)	Data output access time	Slave mode	0	$3t_{HCLK}$	
$t_{v(SO)}$(2)	Data output valid time	Slave mode	-	33	
$t_{v(MO)}$(2)	Data output valid time	Master mode	-	6.5	
$t_{h(SO)}$(2)	Data output hold time	Slave mode	17	-	
$t_{h(MO)}$(2)		Master mode	0.5	-	

1. The characteristics above are given for voltage range 1.
2. Guaranteed by characterization results.
3. The maximum SPI clock frequency in slave transmitter mode is given for an SPI slave input clock duty cycle (DuCy(SCK)) ranging between 40 to 60%.
4. Min time is for the minimum time to drive the output and max time is for the maximum time to validate the data.

Figure 27. Maximum dynamic current consumption on V_{REF+} supply pin during ADC conversion

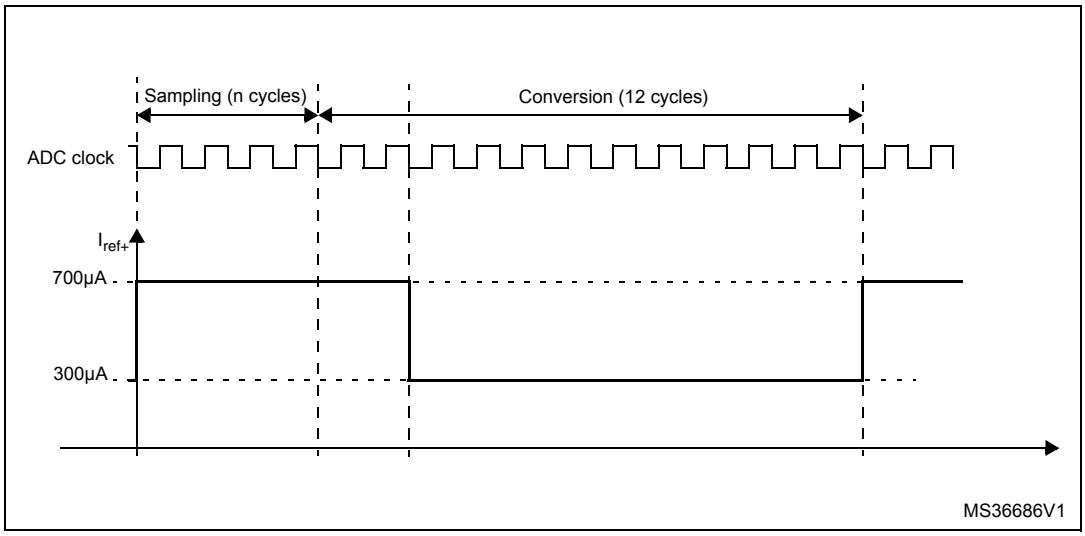


Table 58. Maximum source impedance R_{AIN} max(1)

Ts (µs)	R_{AIN} max (kΩ)				Ts (cycles) f_{ADC}=16 MHz(2)
	Multiplexed channels		Direct channels		
	2.4 V < V_{DDA} < 3.6 V	1.8 V < V_{DDA} < 2.4 V	2.4 V < V_{DDA} < 3.6 V	1.8 V < V_{DDA} < 2.4 V	
0.25	Not allowed	Not allowed	0.7	Not allowed	4
0.5625	0.8	Not allowed	2.0	1.0	9
1	2.0	0.8	4.0	3.0	16
1.5	3.0	1.8	6.0	4.5	24
3	6.8	4.0	15.0	10.0	48
6	15.0	10.0	30.0	20.0	96
12	32.0	25.0	50.0	40.0	192
24	50.0	50.0	50.0	50.0	384

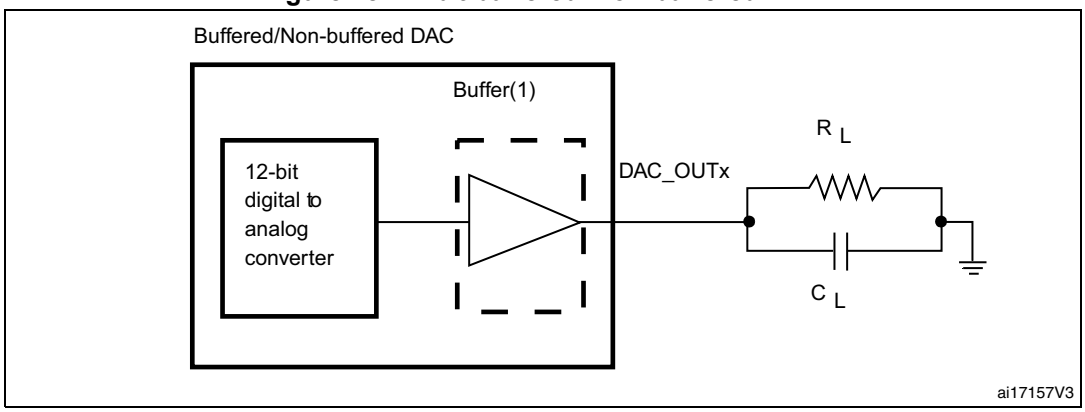
1. Guaranteed by design.
2. Number of samples calculated for f_{ADC} = 16 MHz. For f_{ADC} = 8 and 4 MHz the number of sampling cycles can be reduced with respect to the minimum sampling time Ts (µs),

General PCB design guidelines

Power supply decoupling should be performed as shown in *Figure 9*. The applicable procedure depends on whether V_{REF+} is connected to V_{DDA} or not. The 100 nF capacitors should be ceramic (good quality). They should be placed as close as possible to the chip.

4. Difference between measured value at Code i and the value at Code i on a line drawn between Code 0 and last Code 4095.
5. Difference between the value measured at Code (0x800) and the ideal value = $V_{REF+}/2$.
6. Difference between the value measured at Code (0x001) and the ideal value.
7. Difference between ideal slope of the transfer function and measured slope computed from code 0x000 and 0xFFF when buffer is OFF, and from code giving 0.2 V and (V_{DDA} – 0.2) V when buffer is ON.
8. In buffered mode, the output can overshoot above the final value for low input code (starting from min value).

Figure 28. 12-bit buffered /non-buffered DAC



1. The DAC integrates an output buffer that can be used to reduce the output impedance and to drive external loads directly without the use of an external operational amplifier. The buffer can be bypassed by configuring the BOFFx bit in the DAC_CR register.

6.3.19 Operational amplifier characteristics

Table 60. Operational amplifier characteristics

Symbol	Parameter		Condition(1)	Min(2)	Typ	Max(2)	Unit
CMIR	Common mode input range		-	0	-	V_{DD}	
VI_{OFFSET}	Input offset voltage	Maximum calibration range	-	-	-	±15	mV
		After offset calibration	-	-	-	±1.5	
ΔVI_{OFFSET}	Input offset voltage drift	Normal mode	-	-	-	±40	µV/°C
		Low-power mode	-	-	-	±80	
I_{IB}	Input current bias	Dedicated input	75 °C	-	-	1	nA
		General purpose input		-	-	10	
I_{LOAD}	Drive current	Normal mode	-	-	-	500	µA
		Low-power mode	-	-	-	100	
I_{DD}	Consumption	Normal mode	No load, quiescent mode	-	100	220	µA
		Low-power mode		-	30	60	
CMRR	Common mode rejection ration	Normal mode	-	-	-85	-	dB
		Low-power mode	-	-	-90	-	

6.3.20 Temperature sensor characteristics

Table 61. Temperature sensor calibration values

Calibration value name	Description	Memory address
TS_CAL1	TS ADC raw data acquired at temperature of 30 °C ±5 °C V_{DDA}= 3 V ±10 mV	0x1FF8 00FA - 0x1FF8 00FB
TS_CAL2	TS ADC raw data acquired at temperature of 110 °C ±5 °C V_{DDA}= 3 V ±10 mV	0x1FF8 00FE - 0x1FF8 00FF

Table 62. Temperature sensor characteristics

Symbol	Parameter	Min	Typ	Max	Unit
T_L(1)	V_{SENSE} linearity with temperature	-	±1	±2	°C
Avg_Slope(1)	Average slope	1.48	1.61	1.75	mV/°C
V_{110}	Voltage at 110°C ±5°C(2)	612	626.8	641.5	mV
$I_{DDA(TEMP)}$(3)	Current consumption	-	3.4	6	µA
t_{START}(3)	Startup time	-	-	10	µs
T_{S_temp}(3)	ADC sampling time when reading the temperature	4	-	-	

1. Guaranteed by characterization results.
2. Measured at V_{DD} = 3 V ±10 mV. V110 ADC conversion result is stored in the TS_CAL2 byte.
3. Guaranteed by design.

6.3.21 Comparator

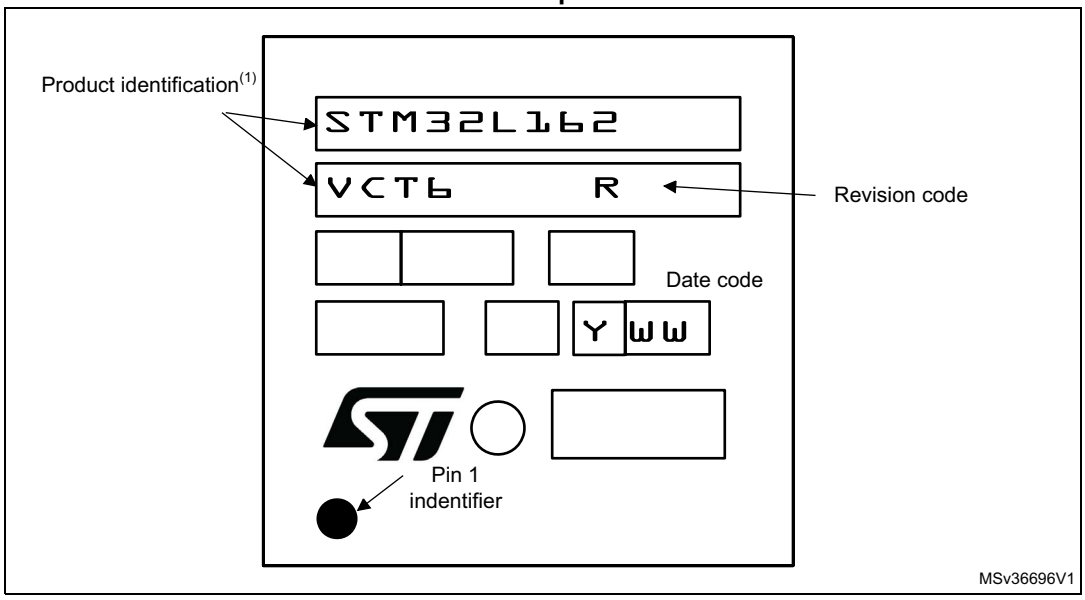
Table 63. Comparator 1 characteristics

Symbol	Parameter	Conditions	Min(1)	Typ	Max(1)	Unit
V_{DDA}	Analog supply voltage	-	1.65		3.6	V
R_{400K}	R_{400K} value	-	-	400	-	kΩ
R_{10K}	R_{10K} value	-	-	10	-	
V_{IN}	Comparator 1 input voltage range	-	0.6	-	V_{DDA}	V
t_{START}	Comparator startup time	-	-	7	10	µs
td	Propagation delay(2)	-	-	3	10	
Voffset	Comparator offset	-	-	±3	±10	mV
$d_{Voffset}$/dt	Comparator offset variation in worst voltage stress conditions	V_{DDA} = 3.6 V V_{IN+} = 0 V V_{IN-} = V_{REFINT} T_A = 25 °C	0	1.5	10	mV/1000 h
I_{COMP1}	Current consumption(3)	-	-	160	260	nA

Marking of engineering samples

The following figure gives an example of topside marking orientation versus pin 1 identifier location.

Figure 31. LQFP100, 14 x 14 mm, 100-pin low-profile quad flat package top view example



1. Parts marked as “ES”, “E” or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering samples to run qualification activity